

# 10V Drive Nch MOSFET

# **R6046ANZ**

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) High ESD.

## Application

Switching

## Packaging specifications

	Package	Bulk	
Type	Code	-	
	Basic ordering unit (pieces)	360	
R6046ANZ	0		

## ● Absolute maximum ratings (Ta = 25°C)

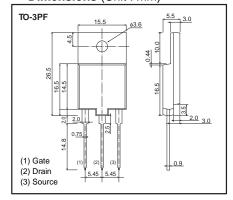
Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	600	V
Gate-source voltage		$V_{GSS}$	±30	V
Drain current	Continuous	I <sub>D</sub> *3	±46	Α
	Pulsed	I <sub>DP</sub> *1	±115	Α
Source current	Continuous	l <sub>S</sub> *3	46	Α
(Body Diode)	Pulsed	I <sub>SP</sub> *1	115	Α
Avalanche current		I <sub>AS</sub> *2	23	Α
Avalanche energy		E <sub>AS</sub> *2	142	mJ
Power dissipation		P <sub>D</sub> *4	120	W
Channel temperature		T <sub>ch</sub>	150	°C
Range of storage temperature		$T_{stg}$	-55 to +150	°C

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

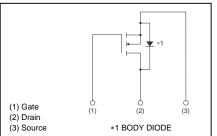
#### • Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	R <sub>th (ch-c)</sub>	1.04	°C/W

#### • Dimensions (Unit : mm)



## • Inner circuit



<sup>\*2</sup> L= 500 $\mu$ H, V<sub>DD</sub>=50V, R<sub>G</sub>=25 $\Omega$ , T<sub>ch</sub>=25°C

<sup>\*3</sup> Limited only by maximum channel temperature allowed.

<sup>\*4</sup> T<sub>C</sub>=25°C

# ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	1	-	±100	nΑ	$V_{GS}=\pm30V$ , $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	1	>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>		-	100	μA	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	2.5	-	4.5	V	$V_{DS}$ =10V, $I_{D}$ =1mA
Static drain-source on-state resistance	R <sub>DS (on)</sub>	-	65	81	mΩ	I <sub>D</sub> =23A, V <sub>GS</sub> =10V
Forward transfer admittance	I Y <sub>fs</sub> I*	19	33	ı	S	$V_{DS}$ =10V, $I_{D}$ =23A
Input capacitance	C <sub>iss</sub>	1	6000	-	pF	V <sub>DS</sub> =25V
Output capacitance	C <sub>oss</sub>	1	3900	1	рF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>		90	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	1	60	-	ns	V <sub>DD</sub> ≒300V, I <sub>D</sub> =23A
Rise time	t <sub>r</sub> *	1	130	1	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	1	230	-	ns	$R_L=13.0\Omega$
Fall time	t <sub>f</sub> *	1	100	1	ns	$R_G=10\Omega$
Total gate charge	Q <sub>g</sub> *	-	150	-	nC	V <sub>DD</sub> ≒300V
Gate-source charge	Q <sub>gs</sub> *	1	35	-	nC	I <sub>D</sub> =46A
Gate-drain charge	Q <sub>gd</sub> *	-	55	-	nC	V <sub>GS</sub> =10V

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	-	-	1.5	V	I <sub>S</sub> =46A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

#### ●Electrical characteristic curves (Ta=25°C)

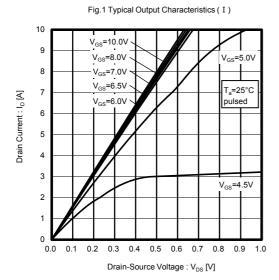


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

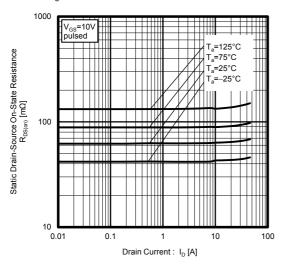


Fig.5 Typical Transfer Characteristics

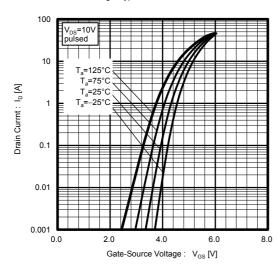


Fig.2 Typical Output Characteristics ( II )

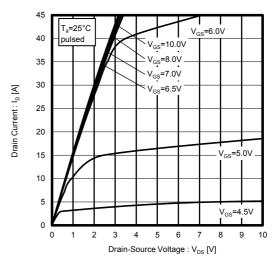


Fig.4 Static Drain-Source On-State Resistance vs. Channel Temperature

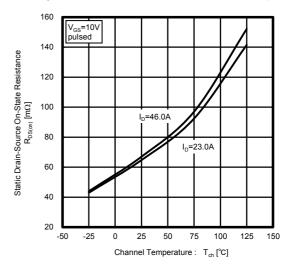


Fig.6 Gate Threshold Voltage vs. Channel Temperature

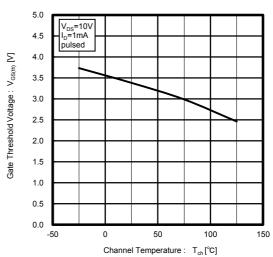


Fig.7 Forward Transfer Admittance vs. Drain Current

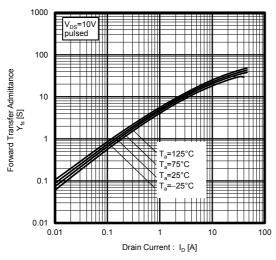


Fig.8 Source Current vs. Source-Drain Voltage

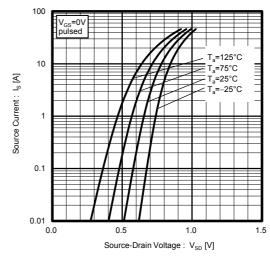


Fig.9 Switching Characteristics

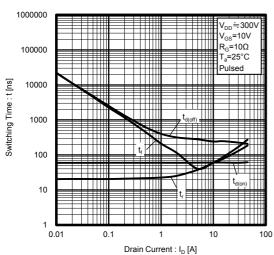


Fig.10 Dynamic Input Characteristics

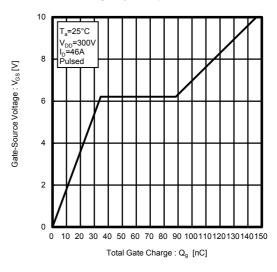


Fig.11 Typical Capacitance vs. Drain-Source Voltage

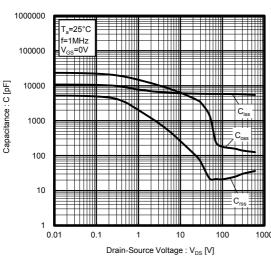
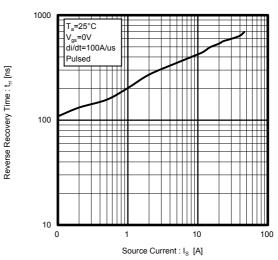


Fig.12 Reverse Recovery Time vs. Source Current



## Measurement circuits

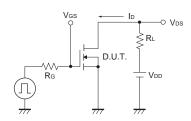


Fig.1-1 Switching Time Measurement Circuit

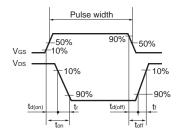


Fig.1-2 Switching Waveforms

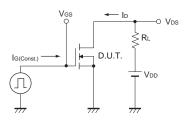


Fig.2-1 Gate Charge Measurement Circuit

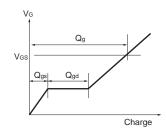


Fig.2-2 Gate Charge Waveform

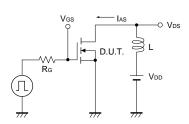


Fig.3-1 Avalanche Measurement Circuit

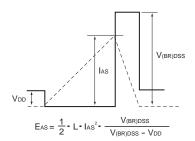


Fig.3-2 Avalanche Waveform

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